



# 32-Channel High Voltage Sample and Hold Amplifier Array

## Features

- ❑ 32 independent high voltage amplifiers
- ❑ 300V operating voltage
- ❑ 295V output voltage
- ❑ 2.2V/ $\mu$ s typical output slew rate
- ❑ Adjustable output current source limit
- ❑ Adjustable output current sink limit
- ❑ Internal closed loop gain of 72V/V
- ❑ 12M $\Omega$  feedback impedance
- ❑ Layout ideal for die applications

## Application

- ❑ MEMS (microelectromechanical systems) driver
- ❑ Piezoelectric transducer driver
- ❑ Optical crosspoint switches (using MEMS technology)

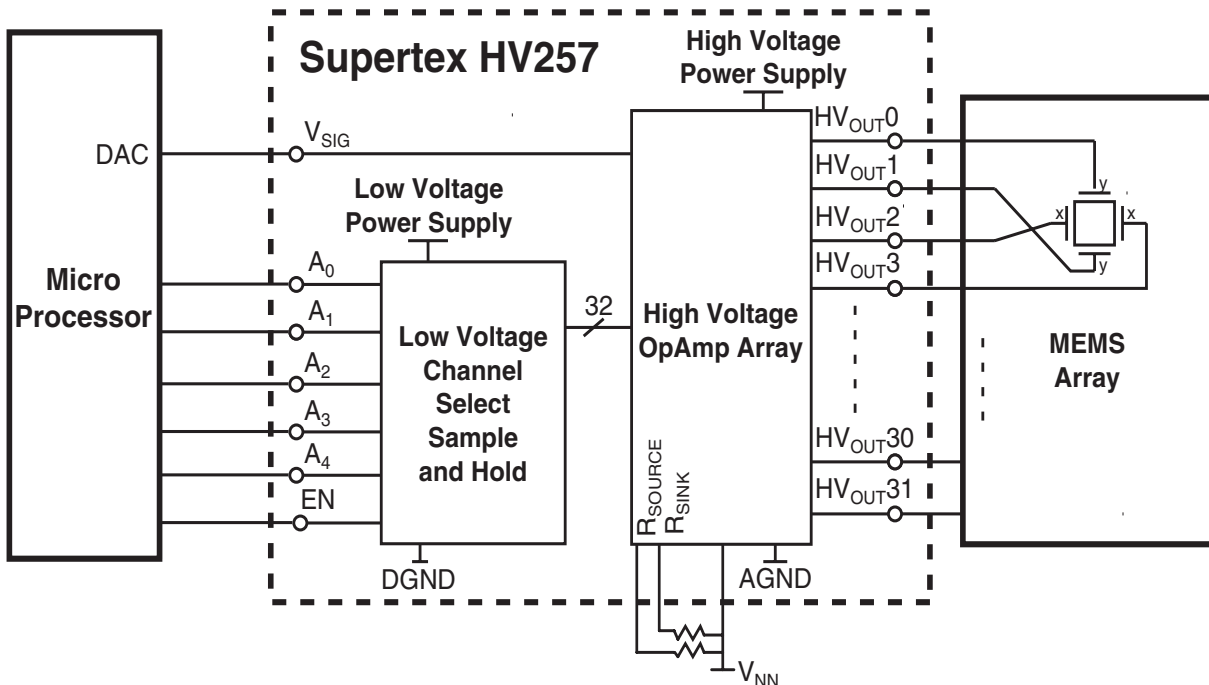
## General Description

The Supertex HV257 is a 32-channel high voltage sample and hold amplifier array integrated circuit. It operates on a single high voltage supply, up to 300V, and two low voltage supplies,  $V_{DD}$  and  $V_{NN}$ .

All 32 sample and hold circuits share a common analog input,  $V_{sig}$ . The individual sample and hold circuits are selected by a 5 to 32 logic decoder. The sampled voltage on the holding capacitor is buffered by a low voltage amplifier and amplified by a high voltage amplifier with a closed loop gain of 72V/V. The internal closed loop gain is set for an input voltage range of 0V to 4.096V. The input voltage can be up to 5.0V, but the output will saturate. The maximum output voltage swing is 5V below the  $V_{PP}$  high voltage supply. The outputs can drive capacitive loads of up to 3000pF.

The maximum output source and sink current can be adjusted by using two external resistors. An external  $R_{SOURCE}$  resistor controls the maximum sourcing current and an external  $R_{SINK}$  resistor controls the maximum sinking current. The current limit is approximately 12.5V divided by the external resistor value. The setting is common for all 32 outputs. A low voltage silicon junction diode is made available to help monitor the die temperature.

## Typical Application



## Ordering Information

Device	Maximum Output Voltage	Nominal Closed Loop Gain	Package Options	
			100Lead MQFP	Die
HV257	295V	72V/V	HV257FG	HV257X

## Absolute Maximum Ratings\*

$V_{PP}$ , High voltage supply	310V
$A_{V_{DD}}$ , Analog low voltage positive supply	8.0V
$DV_{DD}$ , Digital low voltage positive supply	8.0V
$A_{V_{NN}}$ , Analog low voltage negative supply	-7.0V
$DV_{NN}$ , Digital low voltage negative supply	-7.0V
Logic input voltage	-0.5V to $DV_{DD}$
$V_{IN}$ , Analog input signal	0V to 6.0V
Storage temperature range	-65°C to 150°C
Maximum junction temperature	150°C

\*Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

## Electrical Characteristics (Over operating conditions unless otherwise noted.)

Symbol	Parameters	Min	Typ	Max	Unit	Condition
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## Operating Conditions

$V_{PP}$	High voltage positive supply	125		300	V	
$V_{DD}$	Low voltage positive supply	6.0		7.5	V	
$V_{NN}$	Low voltage negative supply	-4.5		-6.5	V	
$I_{PP}$	$V_{PP}$ supply current			0.8	mA	$V_{PP} = 300V$ , All $HV_{OUT} = 0V$ , No Load
$I_{DD}$	$V_{DD}$ supply current			4.3	mA	$V_{DD} = 6.0V$ to $7.5V$
$I_{NN}$	$V_{NN}$ supply current	-5.2			mA	$V_{NN} = -4.5V$ to $-6.5V$
$T_J$	Junction temperature range	-10		125	°C	

## High Voltage Amplifier

$HV_{OUT}$	$HV_{OUT}$ voltage swing	0		$V_{PP} - 5$	V	
$V_{INOS}$	Input voltage offset			$\pm 50$	mV	Input referred.
SR	$HV_{OUT}$ slew rate rise		2.2		V/ $\mu$ s	No Load
	$HV_{OUT}$ slew rate fall		2.0		V/ $\mu$ s	No Load
BW	$HV_{OUT}$ -3dB channel bandwidth		4.0		KHz	$V_{PP} = 300V$
$A_O$	Open loop gain	70	100		dB	
$A_V$	Closed loop gain	68.4	72.0	75.6	V/V	
$R_{FB}$	Feedback resistance from $HV_{OUT}$ to ground	9.6	12		M $\Omega$	
$C_{LOAD}$	$HV_{OUT}$ capacitive load	0		3000	pF	
$I_{SOURCE}$	$HV_{OUT}$ sourcing current limiting range	385	550	715	$\mu$ A	$R_{SOURCE} = 25K\Omega$
$I_{SINK}$	$HV_{OUT}$ sinking current limiting range	385	550	715	$\mu$ A	$R_{SINK} = 25K\Omega$
$R_{SOURCE}$	External resistance range for setting current source limit	25		250	K $\Omega$	
$R_{SINK}$	External resistance range for setting current sink limit	25		250	K $\Omega$	
$CT_{DC}$	DC channel to channel crosstalk	-80			dB	
PSRR	Power supply rejection ratio for $V_{PP}$ , $V_{DD}$ , and $V_{NN}$	-40			dB	

## Sample and Hold

Symbol	Parameter	Min	Typ	Max	Units	Conditions
$V_{PED}$	Pedestal Voltage		1.0		mV	input referred
$R_{SW}$	Sample and Hold Switch resistance		5.0		K $\Omega$	
C	Sample and Hold Capacitor		10	12.0	pF	
$RD_{ROOP}$	Droop rate during hold time relative to input			2.0	V/s	output referred
$V_{SIG}$	Input voltage range	0		5.0	V	

## Logic Decoder

Symbol	Parameter	Min	Typ	Max	Units	Conditions
$T_{SU}$	Set-up time-address to enable	75			ns	
$T_H$	Hold time-address to enable bar	75			ns	
$V_{IH}$	Input logic high voltage	2.4		$V_{DD}$	V	
$V_{IL}$	Input logic low voltage	0		1.2	V	
$I_{IH}$	Input logic high current			1.0	$\mu$ A	$V_{IH} = V_{DD}$
$I_{IL}$	Input logic low current	-1.0			$\mu$ A	$V_{IL} = 0V$

## Diode

Symbol	Parameter	Min	Typ	Max	Units	Conditions
PIV	Peak inverse voltage			5.0	V	cathode to anode
$V_F$	Forward diode drop		0.60		V	$I_f = 100\mu A$ , anode to cathode @ 25°C
$I_F$	Forward diode current			100	$\mu$ A	anode to cathode
$T_C$	$V_F$ temperature coefficient		-2.20		mV/°C	anode to cathode

## Power Up/Down Sequence

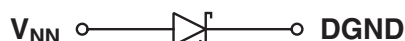
The device can be damaged due to improper power up / down sequence. To prevent damage, please follow the acceptable power up /down sequences and add two external diodes as shown in the diagram below. The first diode is a high voltage diode across  $V_{PP}$  and  $V_{DD}$  where the anode of the diode is connected to  $V_{DD}$  and the cathode of the diode is connected to  $V_{pp}$ . Any low current high voltage diode such as a 1N4004 will be adequate. The second diode is a schottky diode across  $V_{NN}$  and DGnd where the anode of the schottky diode is connected to  $V_{NN}$  and the cathode is connected to DGnd. Any low current schottky diode such as a 1N5817 will be adequate.



**1N4004  
or similar**

### Acceptable Power Up Sequences

- |             |             |             |                   |
|-------------|-------------|-------------|-------------------|
| 1) $V_{PP}$ | 2) $V_{NN}$ | 3) $V_{DD}$ | 4) Inputs & Anode |
| or          |             |             |                   |
| 1) $V_{NN}$ | 2) $V_{DD}$ | 3) $V_{PP}$ | 4) Inputs & Anode |

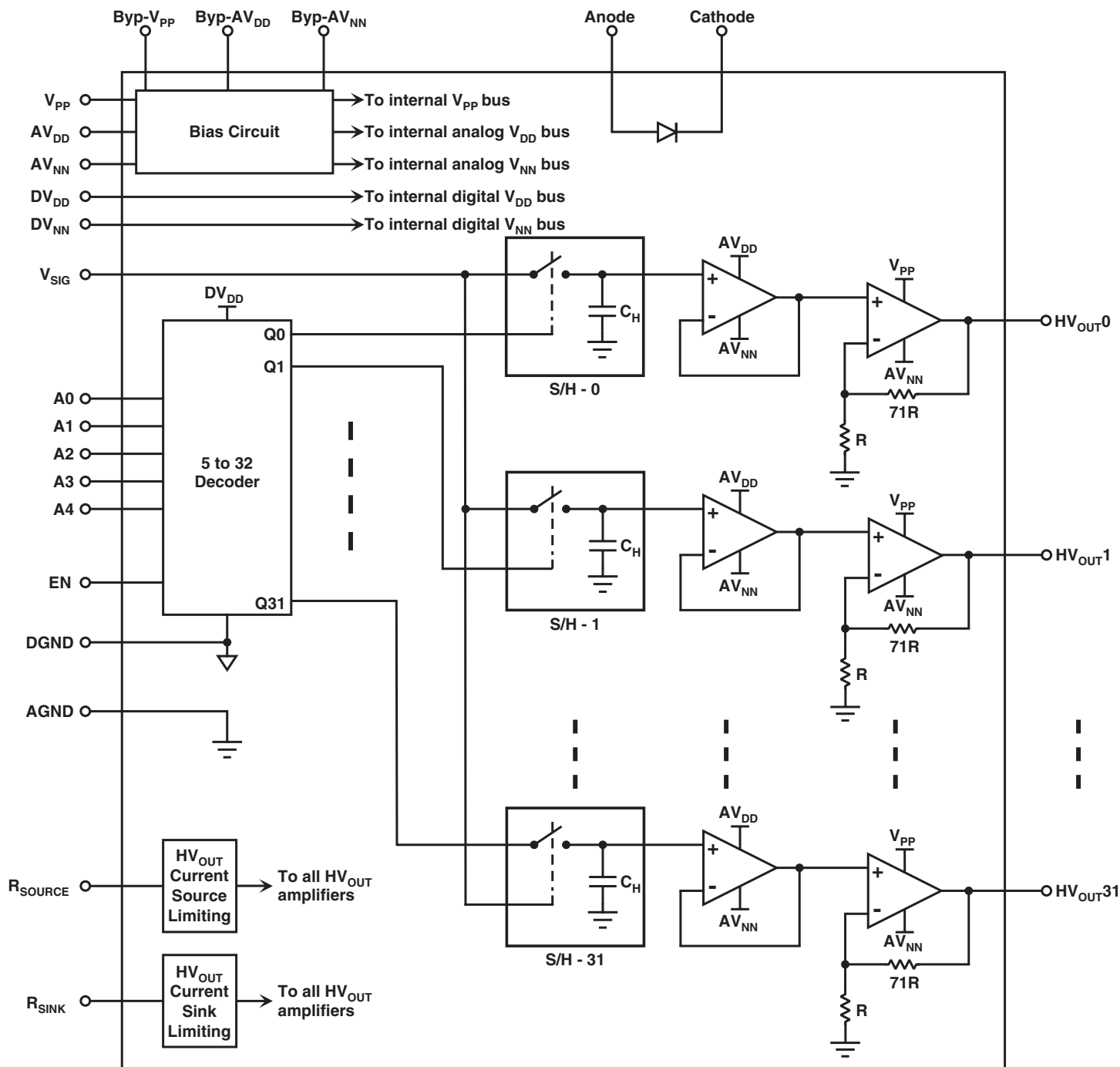


**1N5817  
or similar**

### Acceptable Power Down Sequences

- |                   |             |             |             |
|-------------------|-------------|-------------|-------------|
| 1) Inputs & Anode | 2) $V_{DD}$ | 3) $V_{NN}$ | 4) $V_{PP}$ |
| or                |             |             |             |
| 1) Inputs & Anode | 2) $V_{PP}$ | 3) $V_{DD}$ | 4) $V_{NN}$ |

Block Diagram

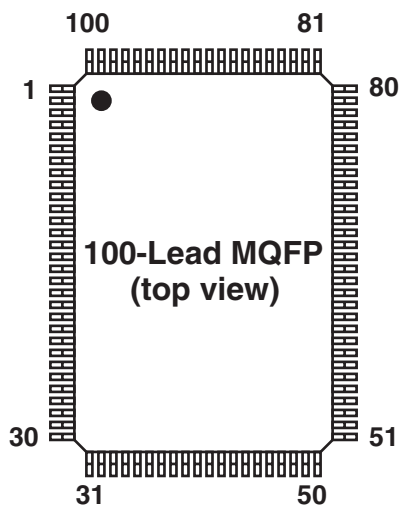


## Truth Table

A4	A3	A2	A1	A0	EN	Selected S/H
L	L	L	L	L	H	0
L	L	L	L	H	H	1
L	L	L	H	L	H	2
L	L	L	H	H	H	3
⋮			⋮			⋮
H	H	H	L	H	H	29
H	H	H	H	L	H	30
H	H	H	H	H	H	31
X	X	X	X	X	L	All Open

## Pin Description

$V_{PP}$	High voltage positive supply. There are two pads.
$B_{YP}-V_{PP}$	A low voltage 1.0 to 10nF decoupling capacitor across $V_{PP}$ and $B_{YP}-V_{PP}$ is required.
$AV_{DD}$	Analog low voltage positive supply. This should be at the same potential as $DV_{DD}$ . There are two pads.
$B_{YP}-AV_{DD}$	A low voltage 1.0 to 10nF decoupling capacitor across $AV_{DD}$ and $B_{YP}-AV_{DD}$ is required.
$AV_{NN}$	Analog low voltage negative supply. This should be the same potential as $DV_{NN}$ . There are two pads.
$B_{YP}-AV_{NN}$	A low voltage 1.0 to 10nF decoupling capacitor across $AV_{NN}$ and $B_{YP}-AV_{NN}$ is required.
$DV_{DD}$	Digital low voltage positive supply. This should be the same potential as $AV_{DD}$ . There are two pads.
$DV_{NN}$	Digital low voltage negative supply. This should be the same potential as $AV_{NN}$ . There are two pads.
DGND	Digital ground
AGND	Analog ground. There are three pads. They need to be externally connected together.
A0 to A4	Decoder logic inputs. Addressed channel will close the sample and hold switch. Sample and hold switches for unaddressed channels are kept open.
EN	Active logic high input. Logic low will keep sample and hold switches open.
Vsig	Common input signal for all 32 sample and hold circuits.
$R_{SOURCE}$	External resistor from $R_{SOURCE}$ to $V_{NN}$ sets output current sourcing limit. Current limit is approximately 12.5V divided by $R_{SOURCE}$ resistor value.
$R_{SINK}$	External resistor from $R_{SINK}$ to $V_{NN}$ sets output current sinking limit. Current limit is approximately 12.5V divided by $R_{SINK}$ resistor value.
Anode	Anode side of a low voltage silicon diode that can be used to monitor die temperature.
Cathode	Cathode side of a low voltage silicon diode that can be used to monitor die temperature.
HV <sub>OUT</sub> 0 to HV <sub>OUT</sub> 31	Amplifier outputs

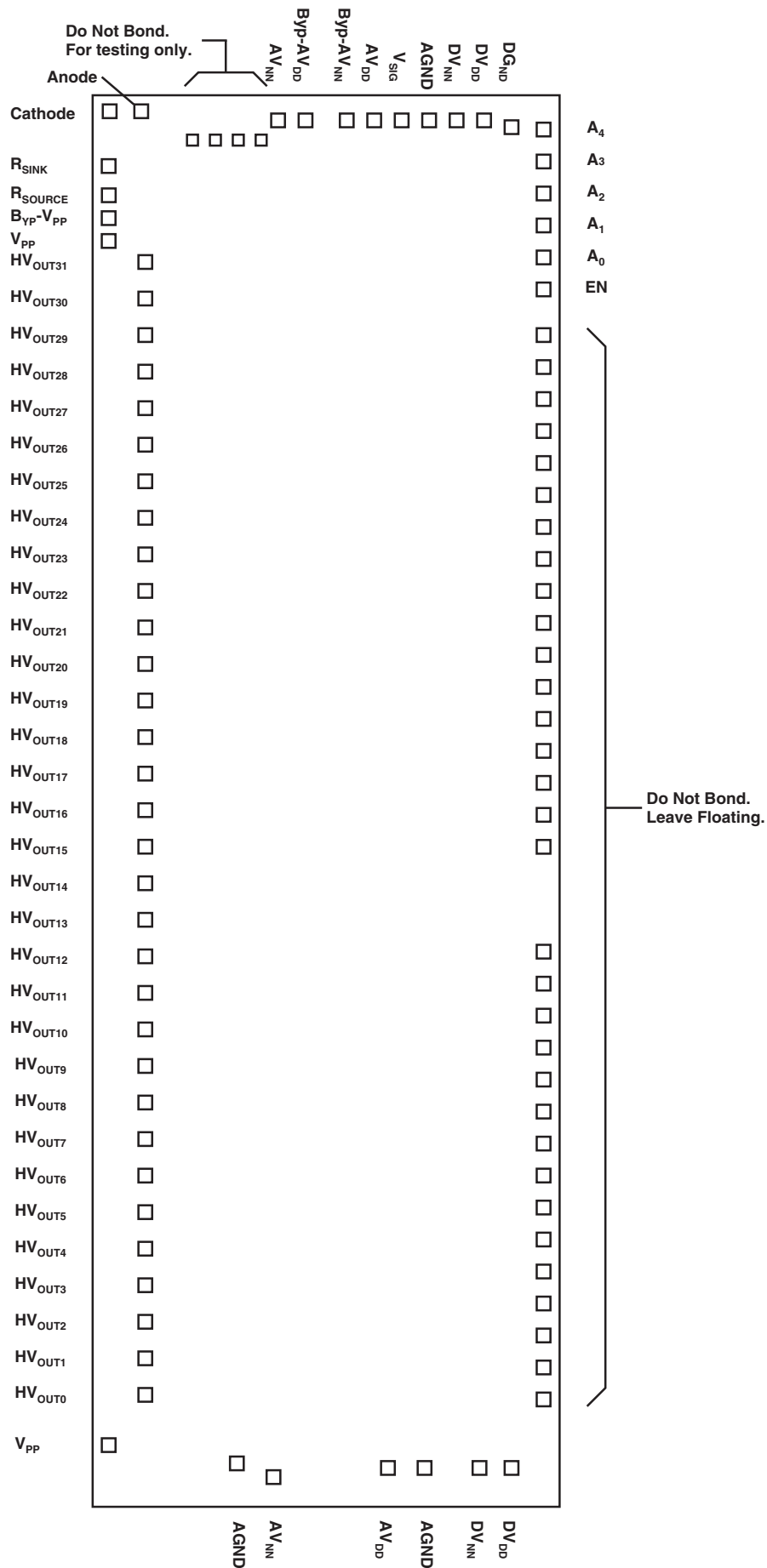


## Pin Configuration

Pin #	Function	Pin #	Function	Pin #	Function	Pin #	Function
1	HV <sub>OUT</sub> 31	26	HV <sub>OUT</sub> 6	51	NC	76	NC
2	HV <sub>OUT</sub> 30	27	HV <sub>OUT</sub> 5	52	NC	77	NC
3	HV <sub>OUT</sub> 29	28	HV <sub>OUT</sub> 4	53	NC	78	NC
4	HV <sub>OUT</sub> 28	29	HV <sub>OUT</sub> 3	54	NC	79	NC
5	HV <sub>OUT</sub> 27	30	HV <sub>OUT</sub> 2	55	NC	80	EN
6	HV <sub>OUT</sub> 26	31	HV <sub>OUT</sub> 1	56	NC	81	A0
7	HV <sub>OUT</sub> 25	32	HV <sub>OUT</sub> 0	57	NC	82	A1
8	HV <sub>OUT</sub> 24	33	V <sub>PP</sub>	58	NC	83	A2
9	HV <sub>OUT</sub> 23	34	NC	59	NC	84	A3
10	HV <sub>OUT</sub> 22	35	NC	60	NC	85	A4
11	HV <sub>OUT</sub> 21	36	NC	61	NC	86	DGND
12	HV <sub>OUT</sub> 20	37	NC	62	NC	87	DV <sub>DD</sub>
13	HV <sub>OUT</sub> 19	38	NC	63	NC	88	DV <sub>NN</sub>
14	HV <sub>OUT</sub> 18	39	AGND	64	NC	89	AGND
15	HV <sub>OUT</sub> 17	40	AV <sub>NN</sub>	65	NC	90	V <sub>SIG</sub>
16	HV <sub>OUT</sub> 16	41	NC	66	NC	91	AV <sub>DD</sub>
17	HV <sub>OUT</sub> 15	42	AV <sub>DD</sub>	67	NC	92	Byp-AV <sub>NN</sub>
18	HV <sub>OUT</sub> 14	43	AGND	68	NC	93	Byp-AV <sub>DD</sub>
19	HV <sub>OUT</sub> 13	44	AV <sub>NN</sub>	69	NC	94	AV <sub>NN</sub>
20	HV <sub>OUT</sub> 12	45	AV <sub>DD</sub>	70	NC	95	Anode
21	HV <sub>OUT</sub> 11	46	NC	71	NC	96	Cathode
22	HV <sub>OUT</sub> 10	47	NC	72	NC	97	R <sub>SINK</sub>
23	HV <sub>OUT</sub> 9	48	NC	73	NC	98	R <sub>SOURCE</sub>
24	HV <sub>OUT</sub> 8	49	NC	74	NC	99	Byp-V <sub>PP</sub>
25	HV <sub>OUT</sub> 7	50	NC	75	NC	100	V <sub>PP</sub>

NC=No Connect.

Pad Configuration *(not drawn to scale)*



## Pad Coordinates

Chip size: 17004 $\mu$ m x 5480 $\mu$ m

Center of die is (0,0)

Pad Name	X ( $\mu$ m)	Y ( $\mu$ m)
V <sub>PP</sub>	-8338.5	2708.5
HV <sub>OUT0</sub>	-7895.0	2305.5
HV <sub>OUT1</sub>	-7448.5	2305.5
HV <sub>OUT2</sub>	-7001.5	2305.5
HV <sub>OUT3</sub>	-6554.5	2305.5
HV <sub>OUT4</sub>	-6107.5	2305.5
HV <sub>OUT5</sub>	-5660.5	2305.5
HV <sub>OUT6</sub>	-5213.5	2305.5
HV <sub>OUT7</sub>	-4766.5	2305.5
HV <sub>OUT8</sub>	-4319.5	2305.5
HV <sub>OUT9</sub>	-3872.5	2305.5
HV <sub>OUT10</sub>	-3425.5	2305.5
HV <sub>OUT11</sub>	-2978.5	2305.5
HV <sub>OUT12</sub>	-2531.5	2305.5
HV <sub>OUT13</sub>	-2084.5	2305.5
HV <sub>OUT14</sub>	-1637.5	2305.5
HV <sub>OUT15</sub>	-1190.5	2305.5
HV <sub>OUT16</sub>	-743.5	2305.5
HV <sub>OUT17</sub>	-296.5	2305.5
HV <sub>OUT18</sub>	150.0	2305.5
HV <sub>OUT19</sub>	597.5	2305.5
HV <sub>OUT20</sub>	1044.5	2305.5
HV <sub>OUT21</sub>	1491.5	2305.5
HV <sub>OUT22</sub>	1938.5	2305.5
HV <sub>OUT23</sub>	2385.5	2305.5
HV <sub>OUT24</sub>	2832.5	2305.5
HV <sub>OUT25</sub>	3279.5	2305.5
HV <sub>OUT26</sub>	3726.5	2305.5
HV <sub>OUT27</sub>	4173.5	2305.5
HV <sub>OUT28</sub>	4620.5	2305.5
HV <sub>OUT29</sub>	5067.5	2305.5

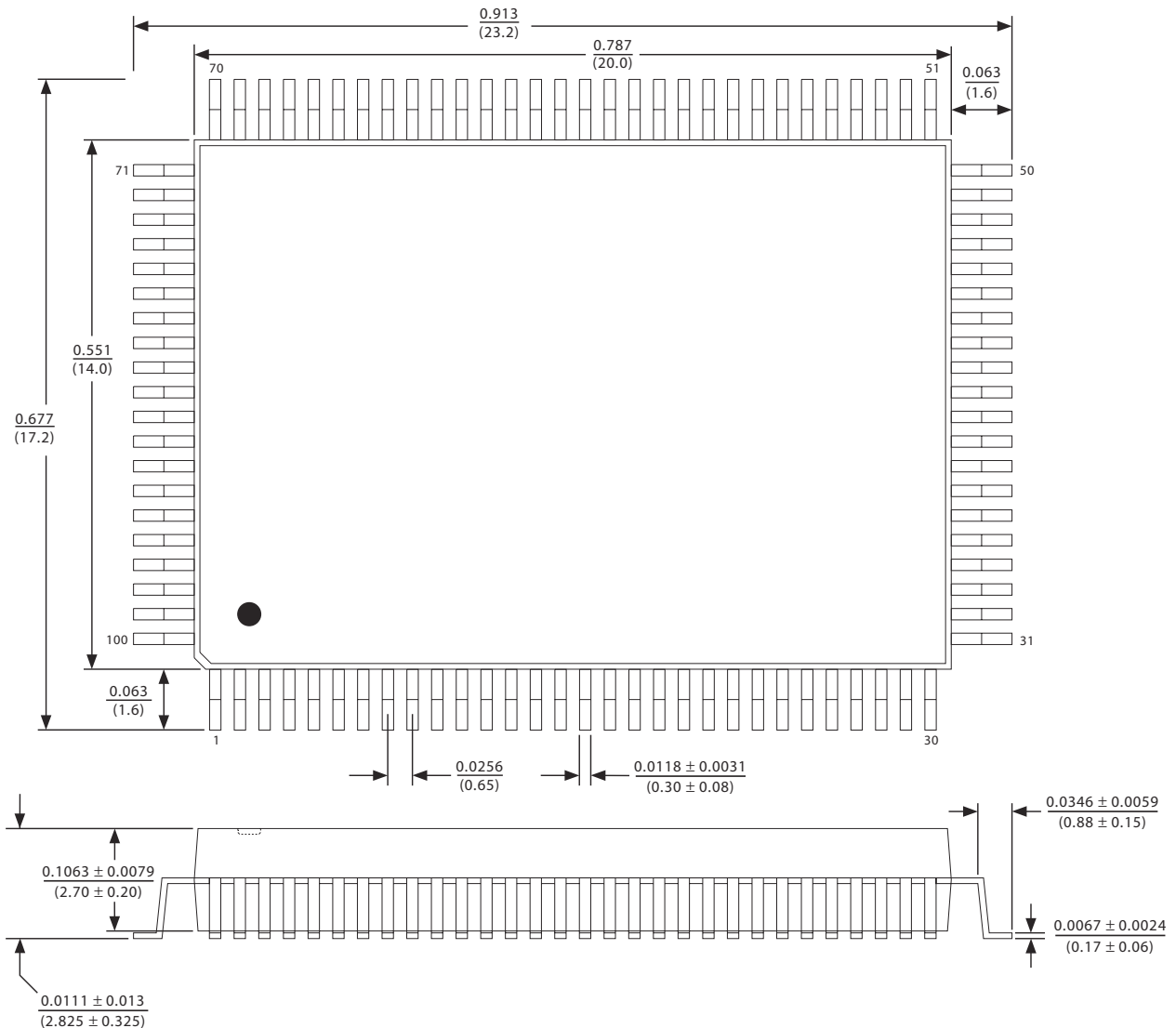
Pad Name	X ( $\mu$ m)	Y ( $\mu$ m)
HV <sub>OUT30</sub>	5514.5	2305.5
HV <sub>OUT31</sub>	5961.5	2305.5
V <sub>PP</sub>	6659	2709
Byp_V <sub>PP</sub>	7045	2709
R <sub>SOURCE</sub>	7489	2709
R <sub>SINK</sub>	7969	2709
Cathode	8366	2709
Anode	8366	2199
AV <sub>NN</sub>	8047	425.0
Byp_AV <sub>DD</sub>	8047	125.5
Byp_AV <sub>NN</sub>	8047	-345.5
AV <sub>DD</sub>	8047	-704.5
V <sub>SIG</sub>	8047	-1072.5
AGND	8047	-1424.5
DV <sub>NN</sub>	8066.5	-1590.0
DV <sub>DD</sub>	8066.5	-1958.5
DGND	7867.0	-2192.0
A4	7723	-2684.0
A3	7319.0	-2684.0
A2	6913.0	-2684.0
A1	6508.5	-2684.0
A0	6103.0	-2684.0
EN	5698.0	-2684.0
NC	5043.5	-2686.0
NC	4638.5	-2686.0
NC	4233.5	-2686.0
NC	3828.5	-2686.0
NC	3423.5	-2686.0
NC	3018.5	-2686.0
NC	2613.5	-2686.0
NC	2208.5	-2686.0

Pad Name	X ( $\mu$ m)	Y ( $\mu$ m)
NC	1803.5	-2686.0
NC	1398.5	-2686.0
NC	993.5	-2686.0
NC	588.5	-2686.0
NC	183.5	-2686.0
NC	-221.5	-2686.0
NC	-626.5	-2686.0
NC	-1031.5	-2686.0
NC	-1436.5	-2686.0
NC	-2412.0	-2686.0
NC	-2817	-2686.0
NC	-3222	-2686.0
NC	-3627	2686.0
NC	-4032	2686.0
NC	-4437	-2686.0
NC	-4842	-2686.0
NC	-5247	-2686.0
NC	-5652	-2686.0
NC	-6052	-2686.0
NC	-6462	-2686.0
NC	-6867	-2686.0
NC	-7272	-2686.0
NC	-7677	-2686.0
NC	-8082	-2686.0
DV <sub>DD</sub>	-8373.0	-2250.0
DV <sub>NN</sub>	-8373.0	-1949.0
AGND	-8367.0	-1561.0
AV <sub>DD</sub>	-8387.0	-1143.0
AV <sub>NN</sub>	-8338.5	577.5
AGND	-8341.0	916.5

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**100 LEAD MQFP PACKAGE OUTLINE (FG)**



Note: Circle (e.g. ⓑ) indicates JEDEC Reference.

Measurement Legend =  $\frac{\text{Dimensions in Inches}}{\text{(Dimensions in Millimeters)}}$